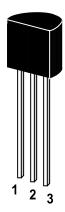
## **PNP Silicon Epitaxial Planar Transistor**

for switching and AF amplifier applications.

The transistor is subdivided into six groups, R, J, H, F, E and K according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base TO-92 Plastic Package Weight approx. 0.19g

## Absolute Maximum Ratings ( $T_a = 25$ °C)

	Symbol	Value	Unit
Collector Base Voltage	-V <sub>CBO</sub>	60	V
Collector Emitter Voltage	-V <sub>CEO</sub>	50	V
Emitter Base Voltage	-V <sub>EBO</sub>	5	V
Collector Current	-I <sub>C</sub>	100	mA
Base Current	-I <sub>B</sub>	20	mA
Power Dissipation	P <sub>tot</sub>	250	mW
Junction Temperature	Tj	150	°C
Storage Temperature Range	Ts	-55 to +150	°C







## **ST 2SA1175**

## Characteristics at T<sub>amb</sub>=25 °C

	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain					
at -V <sub>CE</sub> =6V, -I <sub>C</sub> =2mA					
Current Gain Group R	h <sub>FE</sub>	110	-	180	-
J	h <sub>FE</sub>	135	-	220	-
н	h <sub>FE</sub>	170	-	270	-
F	h <sub>FE</sub>	200	-	320	-
E	h <sub>FE</sub>	250	-	400	-
К	h <sub>FE</sub>	300	-	600	-
Collector Cutoff Current					
at -V <sub>CB</sub> =60V	-I <sub>CBO</sub>	-	-	0.1	μΑ
Emitter Cutoff Current					
at -V <sub>EB</sub> =5V	-I <sub>EBO</sub>	-	-	0.1	μΑ
Collector Saturation Voltage					
at -I <sub>C</sub> =100mA, -I <sub>B</sub> =10mA	-V <sub>CE(sat)</sub>	-	0.18	0.3	V
Gain Bandwidth Product					
at -V <sub>CE</sub> =6V, -I <sub>E</sub> =1mA	$f_T$	50	80	-	MHz
Noise Figure					
at -V <sub>CE</sub> =6V, -I <sub>C</sub> =1V, R <sub>G</sub> =10k $\Omega$ , f=100Hz	NF	-	6	20	dB
Output Capacitance					
at -V <sub>CB</sub> =10V, f=1MHz	$C_OB$	-	4.5	6	pF



